



SEMIPACK® 1

## Thyristor / Diode Modules

## SKKH 60/16 E

## Features\*

- Heat transfer through aluminium oxide ceramic insulated metal baseplate
- UL recognized, file no. E63532

## Typical Applications

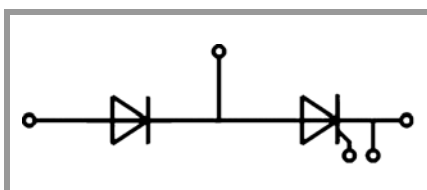
- Rectifier for motor drives
- Process control
- Rectifier for power supplies

## Absolute Maximum Ratings

| Symbol                | Conditions                              |                       | Values      | Unit |
|-----------------------|-----------------------------------------|-----------------------|-------------|------|
| Thyristor / diode     |                                         |                       |             |      |
| $I_{F(AV)}/I_{T(AV)}$ | sin. 180°                               | $T_c = 85\text{ °C}$  | 60          | A    |
|                       | $T_j = 130\text{ °C}$                   | $T_c = 100\text{ °C}$ | 46          | A    |
| $I_{FSM}/I_{TSM}$     | $t_p = 10\text{ ms}$                    | $T_j = 25\text{ °C}$  | 1100        | A    |
|                       |                                         | $T_j = 130\text{ °C}$ | 900         | A    |
| $i^2t$                | $t_p = 10\text{ ms}$                    | $T_j = 25\text{ °C}$  | 6050        | A²s  |
|                       |                                         | $T_j = 130\text{ °C}$ | 4050        | A²s  |
| $V_{RSM}$             | $T_j = 25\text{ °C}$ , thyristor, diode |                       | 1700        | V    |
| $V_{RRM}$             | $T_j = 25\text{ °C}$ , thyristor, diode |                       | 1600        | V    |
| $V_{DRM}$             | $T_j = 25\text{ °C}$ , thyristor        |                       | 1600        | V    |
| $(di/dt)_{cr}$        | $T_j = 130\text{ °C}$ , thyristor       |                       | 50          | A/μs |
| $(dv/dt)_{cr}$        | $T_j = 130\text{ °C}$ , thyristor       |                       | 1000        | V/μs |
| $T_j$                 |                                         |                       | -40 ... 130 | °C   |
| Module                |                                         |                       |             |      |
| $T_{stg}$             |                                         |                       | -40 ... 125 | °C   |
| $V_{isol}$            | a.c.; 50 Hz; r.m.s.                     | 1 min                 | 3000        | V    |
|                       |                                         | 1 s                   | 3600        | V    |

## Characteristics

| Symbol           | Conditions                                                      | min. | typ.                 | max. | Unit |
|------------------|-----------------------------------------------------------------|------|----------------------|------|------|
| <b>Thyristor</b> |                                                                 |      |                      |      |      |
| $V_T$            | $T_j = 25\text{ °C}$ , $I_T = 180\text{ A}$                     |      |                      | 1.85 | V    |
| $V_{T(TO)}$      | $T_j = 130\text{ °C}$                                           |      |                      | 0.92 | V    |
| $r_T$            | $T_j = 130\text{ °C}$                                           |      |                      | 5.8  | mΩ   |
| $I_{DD}; I_{RD}$ | $T_j = 130\text{ °C}$ , $V_{DD} = V_{DRM}$ ; $V_{RD} = V_{RRM}$ |      |                      | 15   | mA   |
| $t_{gd}$         | $I_G = 1\text{ A}$                                              |      | $T_j = 25\text{ °C}$ | 1    | μs   |
| $t_{gr}$         | $di_G/dt = 1\text{ A/μs}$                                       |      | $T_j = 25\text{ °C}$ | 2    | μs   |
|                  | $V_D = 0.67 \cdot V_{DRM}$                                      |      |                      |      |      |
| $t_q$            | $T_j = 130\text{ °C}$                                           |      | 110                  |      | μs   |
| $I_H$            | $T_j = 25\text{ °C}$                                            |      |                      | 220  | mA   |
| $I_L$            | $T_j = 25\text{ °C}$ , $R_G = 33\text{ Ω}$                      |      |                      | 550  | mA   |
| $V_{GT}$         | $T_j = 25\text{ °C}$ , d.c.                                     | 2.5  |                      |      | V    |
| $I_{GT}$         | $T_j = 25\text{ °C}$ , d.c.                                     | 100  |                      |      | mA   |
| $V_{GD}$         | $T_j = 130\text{ °C}$ , d.c.                                    |      |                      | 0.25 | V    |
| $I_{GD}$         | $T_j = 130\text{ °C}$ , d.c.                                    |      |                      | 4    | mA   |
| $R_{th(j-c)}$    | cont., per chip                                                 |      |                      | 0.32 | K/W  |
|                  | sin. 180°, per chip                                             |      |                      | 0.42 | K/W  |
|                  | rec. 120°, per chip                                             |      |                      | 0.44 | K/W  |
| <b>Diode</b>     |                                                                 |      |                      |      |      |
| $V_F$            | $T_j = 25\text{ °C}$ , $I_F = 180\text{ A}$                     |      |                      | 1.55 | V    |
| $V_{F0}$         | $T_j = 130\text{ °C}$                                           |      |                      | 0.85 | V    |
| $r_F$            | $T_j = 130\text{ °C}$                                           |      |                      | 3.90 | mΩ   |
| $I_R$            | $T_j = 130\text{ °C}$ , $V_{RD} = V_{RRM}$                      |      |                      | 1.7  | mA   |
| $R_{th(j-c)}$    | cont., per chip                                                 |      |                      | 0.3  | K/W  |
|                  | sin. 180°, per chip                                             |      |                      | 0.38 | K/W  |
|                  | rec. 120°, per chip                                             |      |                      | 0.4  | K/W  |



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| Characteristics |                            |      |      |          |                  |
|-----------------|----------------------------|------|------|----------|------------------|
| Symbol          | Conditions                 | min. | typ. | max.     | Unit             |
| Module          |                            |      |      |          |                  |
| $R_{th(c-s)}$   | thyristor, P12 (reference) |      | 0.09 |          | K/W              |
|                 | diode, P12 (reference)     |      | 0.09 |          | K/W              |
|                 | module, P12 (reference)    |      | 0.05 |          | K/W              |
| $M_s$           | to heatsink M5             | 4.25 |      | 5.75     | Nm               |
| $M_t$           | to terminals M5            | 2.55 |      | 3.45     | Nm               |
| a               |                            |      |      | 5 * 9.81 | m/s <sup>2</sup> |
| w               |                            |      | 75   |          | g                |

## Thyristor / Diode Modules

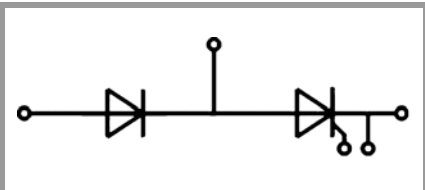
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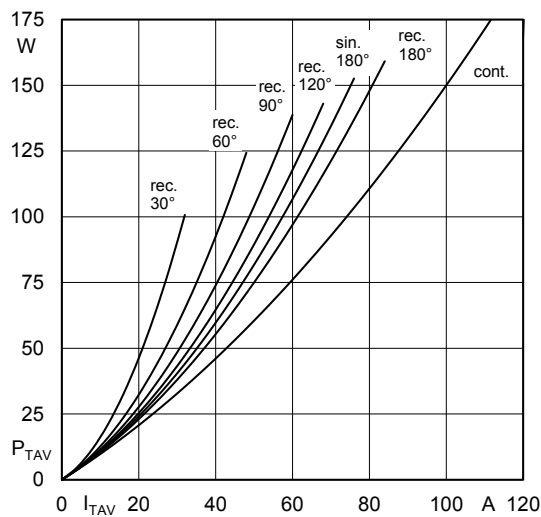


Fig. 1L: Power dissipation per thyristor vs. on-state current

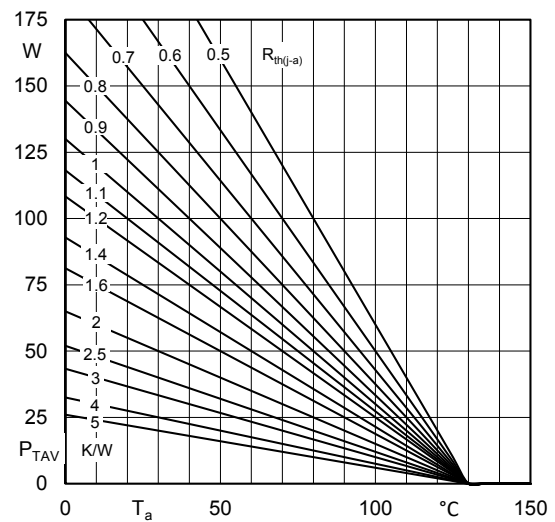


Fig. 1R: Max. power dissipation per thyristor vs. ambient temperature

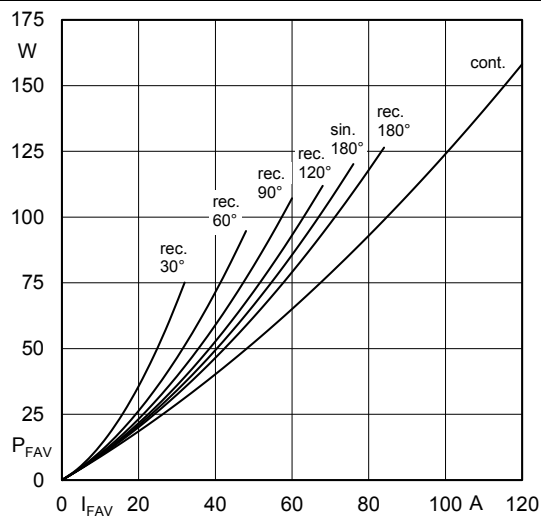


Fig. 2L: Power dissipation per diode vs. forward current

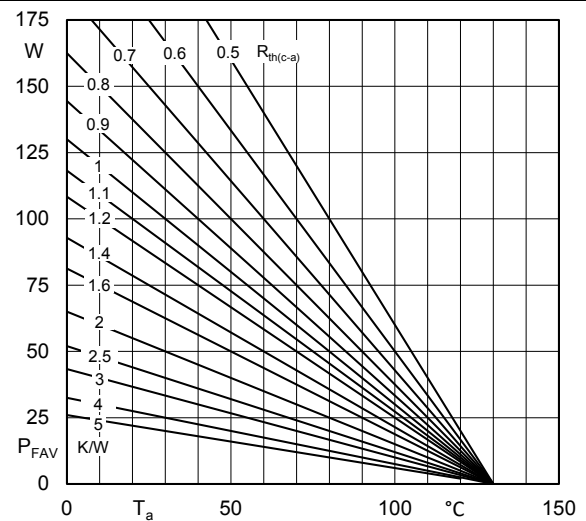


Fig. 2R: Max power dissipation per diode vs. ambient temperature

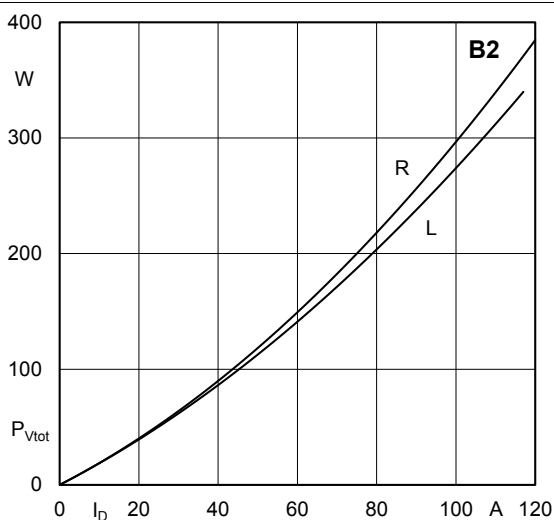


Fig. 3L: Max. power dissipation of two modules vs. direct current

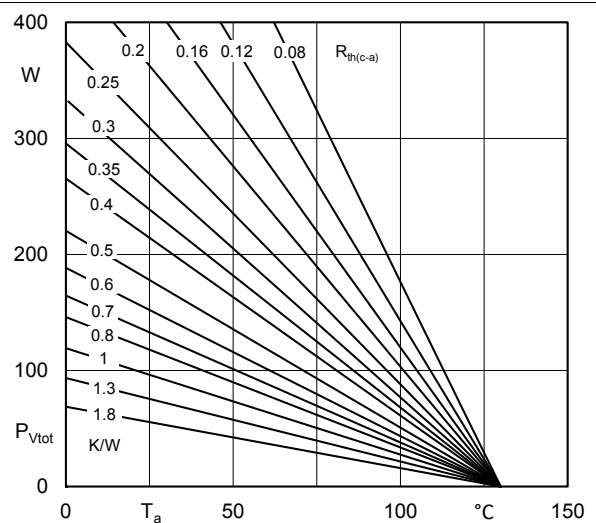


Fig. 3R: Max. power dissipation of two modules vs. case temperature

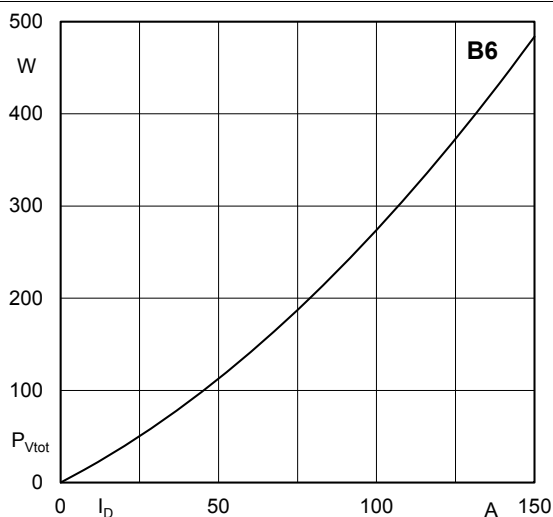


Fig. 4L: Max. power dissipation of three modules vs. direct current

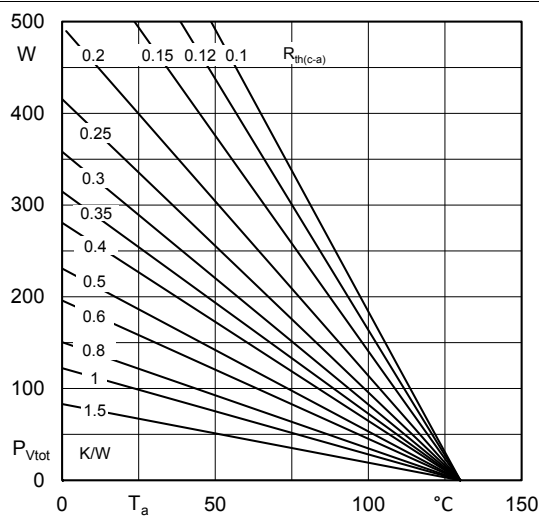


Fig. 4R: Max. power dissipation of three modules vs. ambient temperature

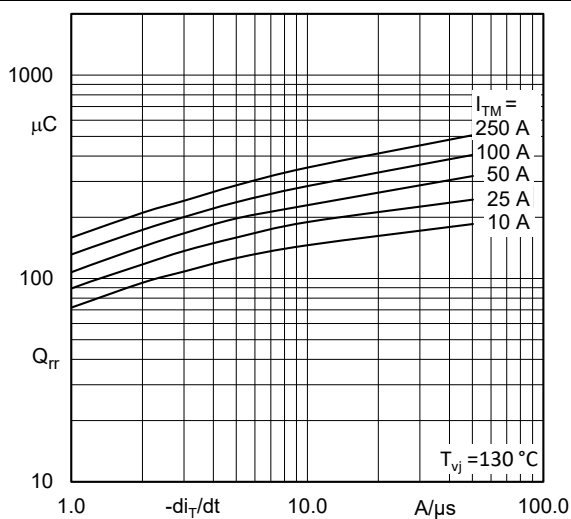


Fig. 5: Recovered charge vs. current decrease

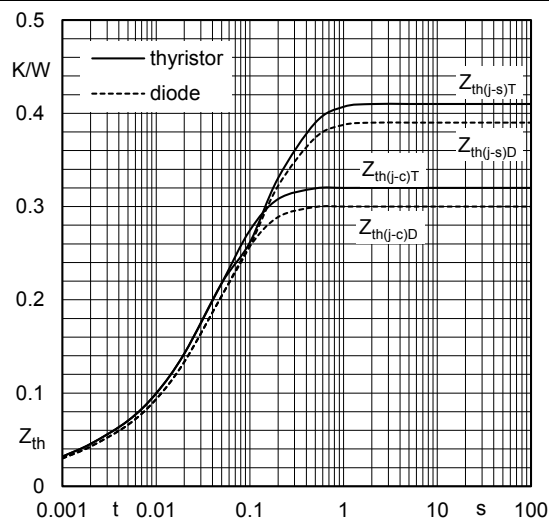


Fig. 6: Transient thermal impedance vs. time

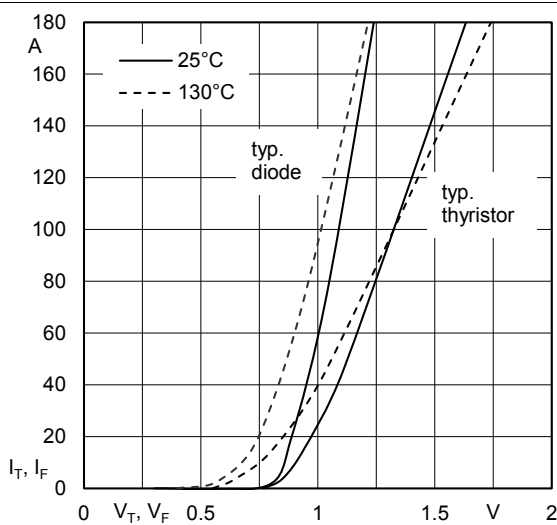


Fig. 7: On-state characteristics

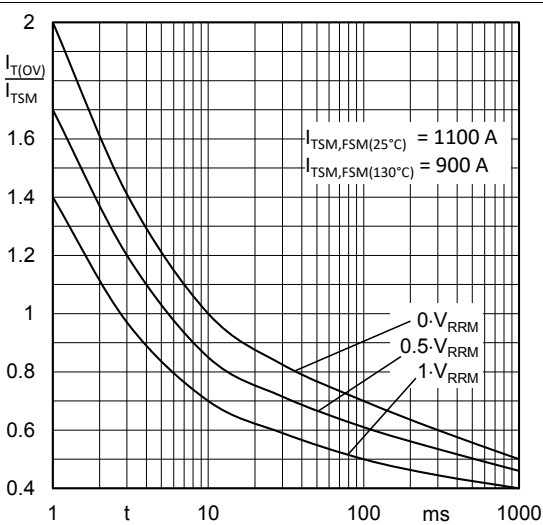


Fig. 8: Surge overload current vs. time

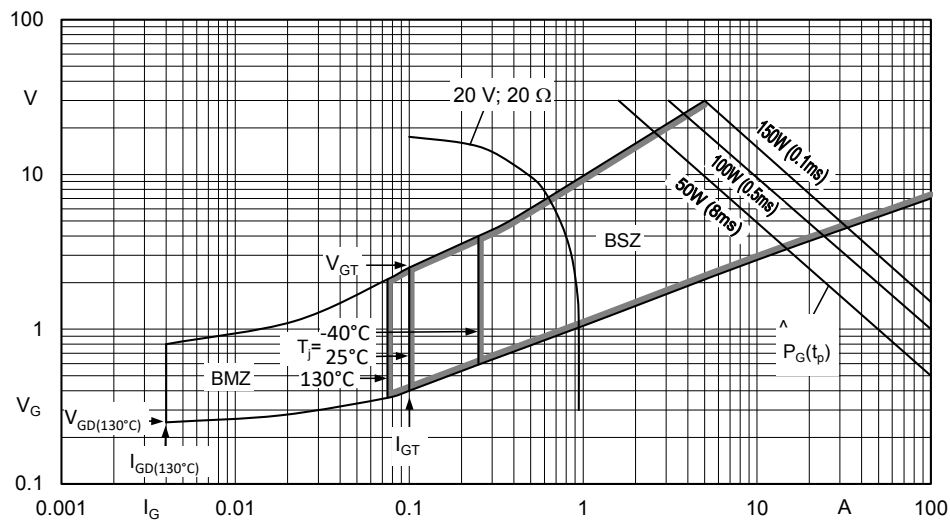
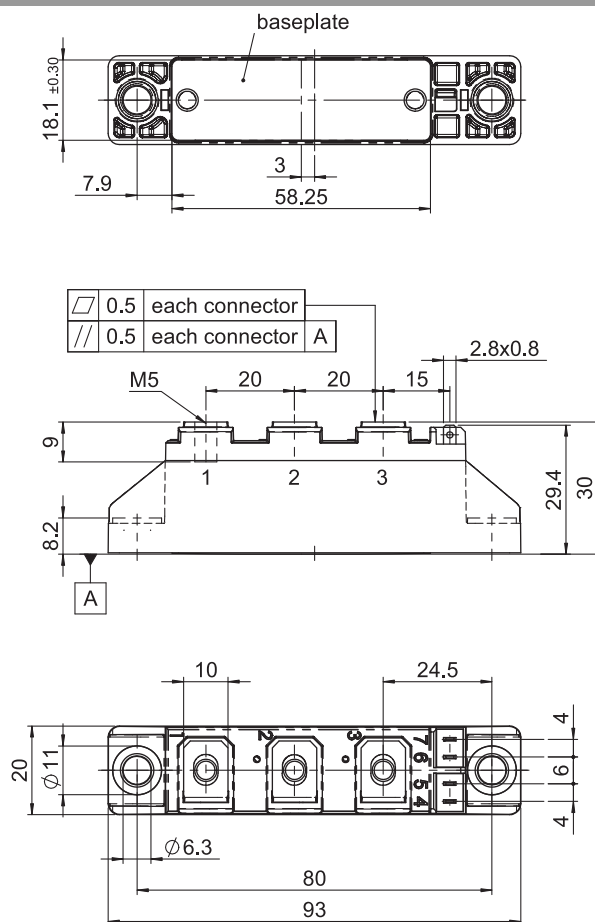
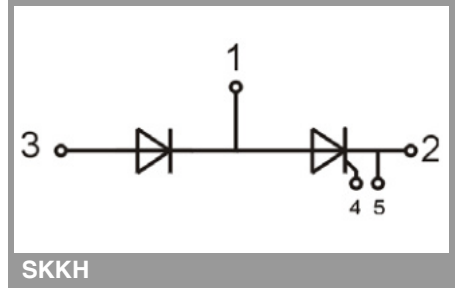


Fig. 9: Gate trigger characteristics



general tolerance  $\pm 0.5\text{mm}$

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## IMPORTANT INFORMATION AND WARNINGS

This is an electrostatic discharge sensitive device (ESDS) according to international standard IEC 61340.

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